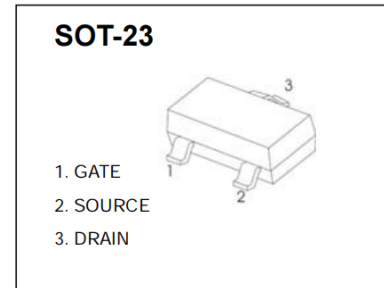


Plastic-Encapsulate MOSFETS

N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20 V	380mΩ@ 4.5V	0.75A
	450mΩ@ 2.5V	
	800mΩ@ 1.8V	



FEATURES

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

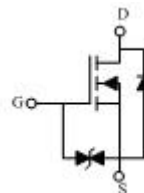
APPLICATION

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Typical Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current (note 1)	I_D	0.75	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	1.8	A
Power Dissipation (note 1)	P_D	350	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" duration for 10 s)	T_L	260	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage (note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.35	0.54	1.1	V
Drain-source on-resistance (note 2)	R _{DS(on)}	V _{GS} =4.5V, I _D =0.65A		270	380	mΩ
		V _{GS} =2.5V, I _D =0.55A		320	450	mΩ
		V _{GS} =1.8V, I _D =0.45A		390	800	mΩ
Forward transconductance (note 2)	g _{FS}	V _{DS} =10V, I _D =0.8A		1.6		S
Diode forward voltage	V _{SD}	I _S =0.15A, V _{GS} = 0V			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C _{iss}	V _{DS} =16V, V _{GS} =0V, f =1MHz		79	120	pF
Output capacitance	C _{oss}			13	20	pF
Reverse transfer capacitance	C _{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	t _{d(on)}	V _{GS} =4.5V, V _{DS} =10V, I _D =500mA, R _{GEN} =10Ω		6.7		ns
Turn-on rise time (note 3)	t _r			4.8		ns
Turn-off delay time (note 3)	t _{d(off)}			17.3		ns
Turn-off fall time (note 3)	t _f			7.4		ns

Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producing.

Typical Characteristics

